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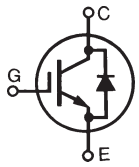
IXYS

1200V XPT™ IGBT GenX3™ w/ Diode

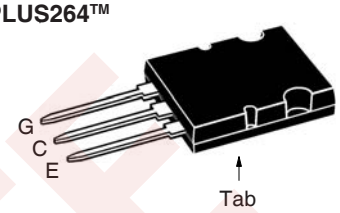
IXYB82N120C3H1

V_{CES} = 1200V
I_{C110} = 82A
$V_{CE(sat)}$ ≤ 3.2V
$t_{fi(typ)}$ = 93ns

High-Speed IGBT
for 20-50 kHz Switching



PLUS264™



G = Gate C = Collector
E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	1200	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	1200	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C (Chip Capability)	164	A
I_{LRMS}	Lead Current Limit	160	A
I_{C110}	T_C = 110°C	82	A
I_{F110}	T_C = 110°C	42	A
I_{CM}	T_C = 25°C, 1ms	320	A
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 125°C, R_G = 2Ω Clamped Inductive Load	I_{CM} = 164 @$V_{CE} \leq V_{CES}$	A
P_C	T_C = 25°C	1040	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
F_C	Mounting Force	30..120 / 6.7..27	N/lb.
Weight		10	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	1200			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.0		5.0	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			50	μA
	T_J = 125°C			3	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 82A, V_{GE} = 15V, Note 1		2.75	3.20	V
	T_J = 125°C		3.50		V

Features

- Optimized for Low Switching Losses
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- Positive Thermal Coefficient of Vce(sat)
- High Current Handling Capability
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

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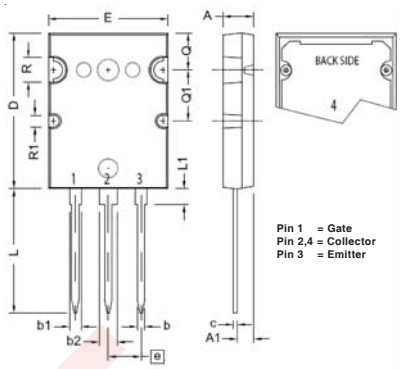
IXYS IXYB82N120C3H1

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 60A, V_{CE} = 10V, Note 1	30	50		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		4060		pF
C_{oes}			285		pF
C_{res}			110		pF
$Q_{g(on)}$	I_C = 82A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		215		nC
Q_{ge}			26		nC
Q_{gc}			84		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		29		ns
t_{ri}	I_C = 80A, V_{GE} = 15V		78		ns
E_{on}	V_{CE} = 0.5 • V_{CES}, R_G = 2Ω		4.95		mJ
$t_{d(off)}$	Note 2		192	280	ns
t_{fi}			93		ns
E_{off}			2.78	5.00	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		29		ns
t_{ri}	I_C = 80A, V_{GE} = 15V		90		ns
E_{on}	V_{CE} = 0.5 • V_{CES}, R_G = 2Ω		7.45		mJ
$t_{d(off)}$	Note 2		200		ns
t_{fi}			95		ns
E_{off}			3.70		mJ
R_{thJC}				0.12	°C/W
R_{thCS}			0.13		°C/W

PLUS264™ (IXYB) Outline



Dim.	Millimeter min	Millimeter max	Inches min	Inches max
A	4.70	5.31	0.185	0.209
A1	2.59	3.00	0.102	0.118
b	0.94	1.40	0.037	0.055
b1	2.21	2.59	0.087	0.102
b2	2.79	3.20	0.110	0.126
c	0.43	0.74	0.017	0.029
D	25.58	26.59	1.007	1.047
E	19.30	20.29	0.760	0.799
e	5.45 BSC		0.215 BSC	
L	19.79	21.39	0.779	0.842
L1	2.21	2.59	0.087	0.102
Q	6.10	6.50	0.240	0.256
Q1	8.38	8.79	0.330	0.346
Ø R	3.94	4.75	0.155	0.187
ØR1	2.16	2.36	0.085	0.093

Reverse Diode (FRED)

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
V_F	I_F = 60A, V_{GE} = 0V, Note 1			2.7	V
	T_J = 125°C		1.9		V
I_{RM}	I_F = 60A, V_{GE} = 0V, T_J = 125°C		41		A
t_{rr}	$-di_F/dt$ = 700A/µs, V_R = 600V		420		ns
R_{thJC}				0.35	°C/W

Notes:

1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25°C

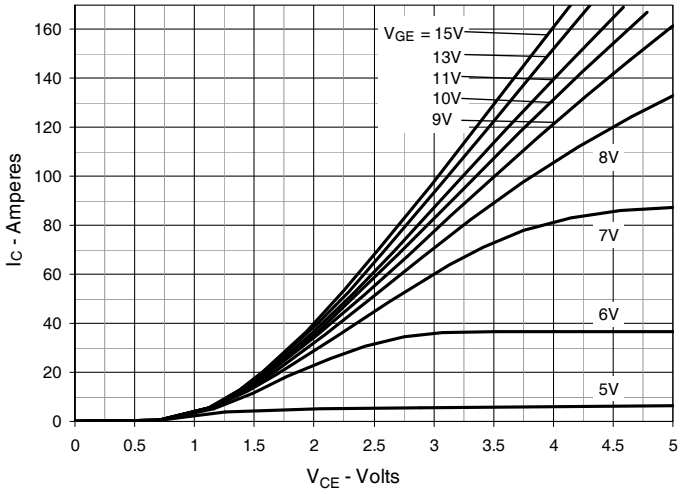


Fig. 2. Extended Output Characteristics @ T_J = 25°C

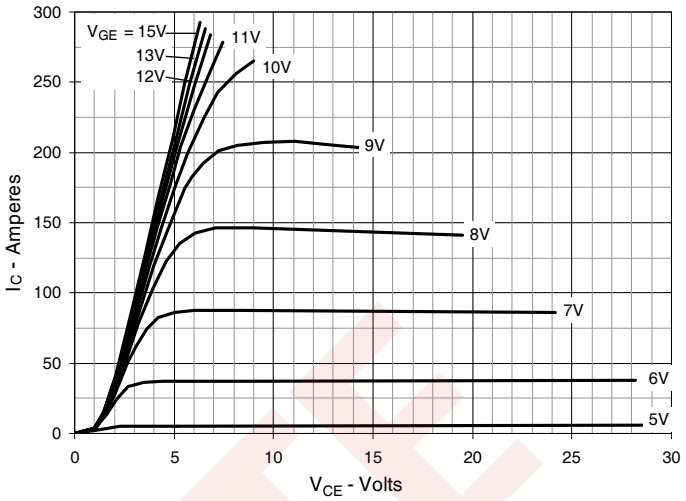


Fig. 3. Output Characteristics @ T_J = 125°C

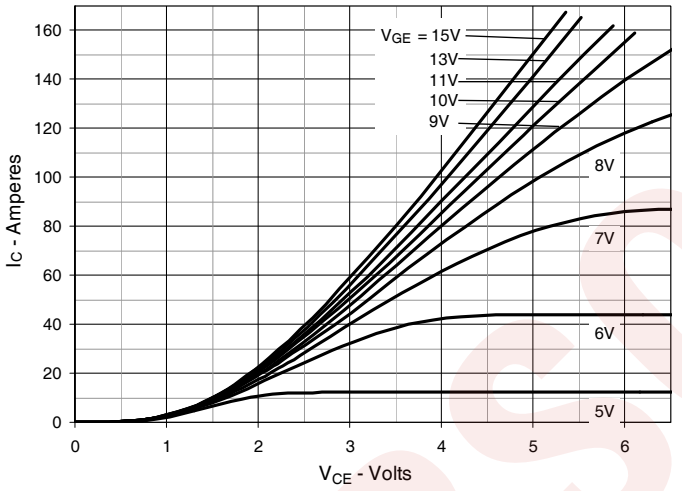


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

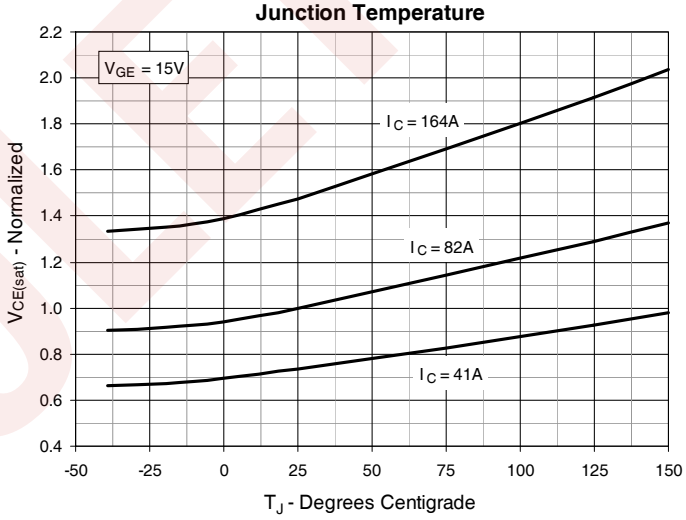


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

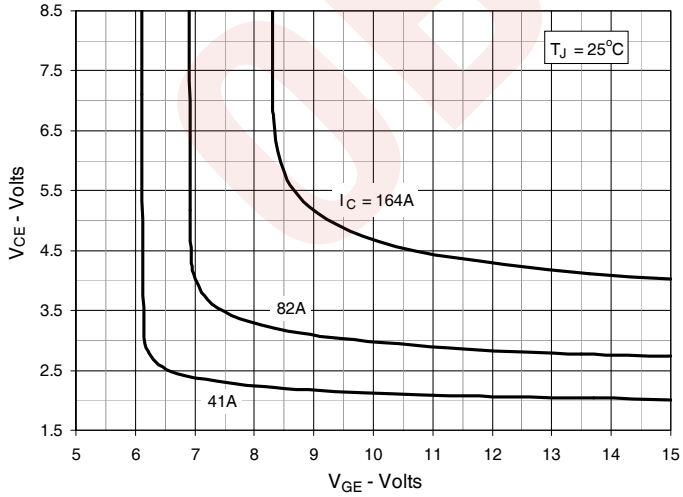


Fig. 6. Input Admittance

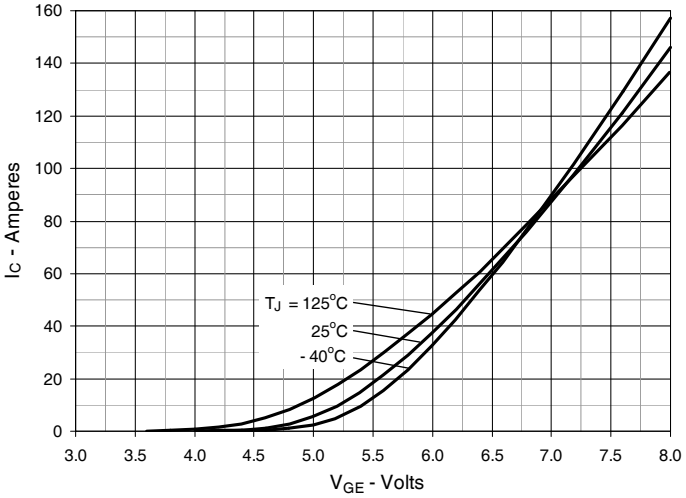


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Fig. 7. Transconductance

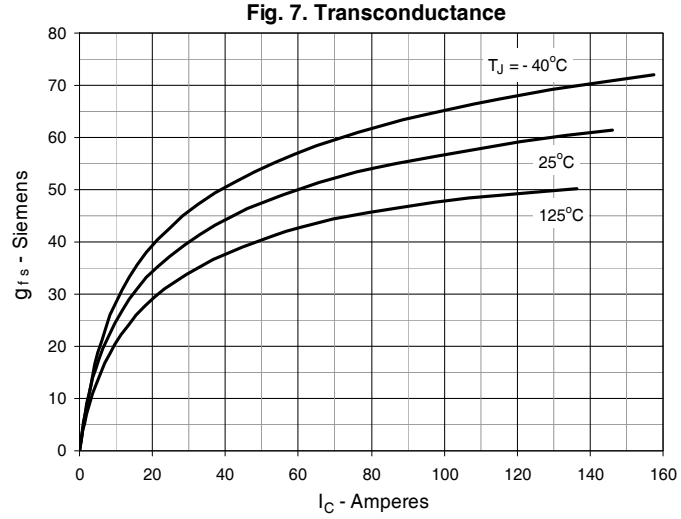


Fig. 8. Gate Charge

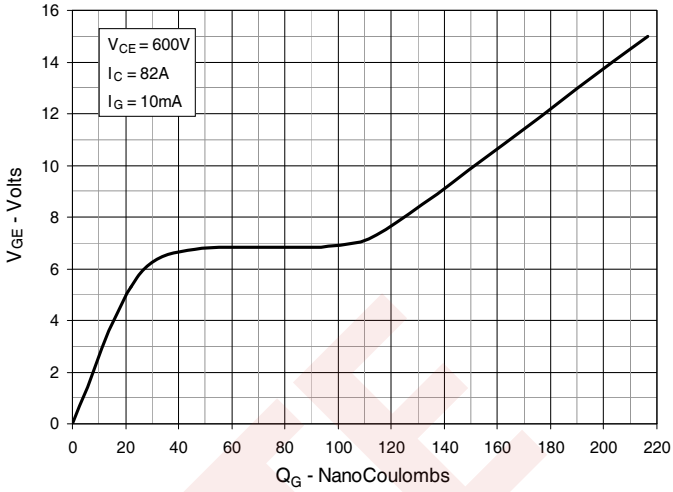


Fig. 9. Capacitance

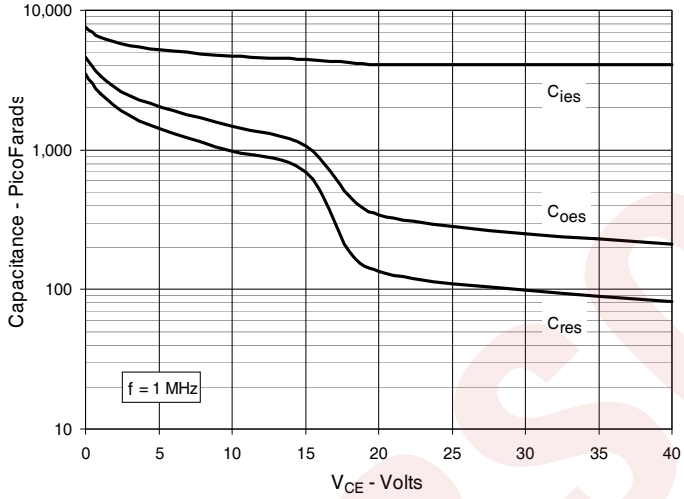


Fig. 10. Reverse-Bias Safe Operating Area

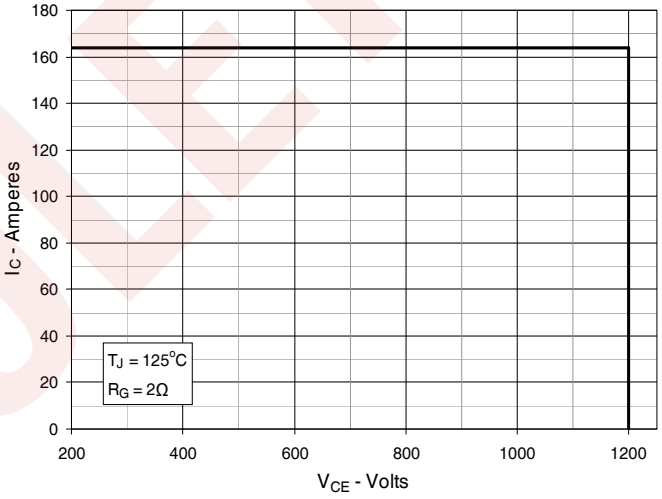
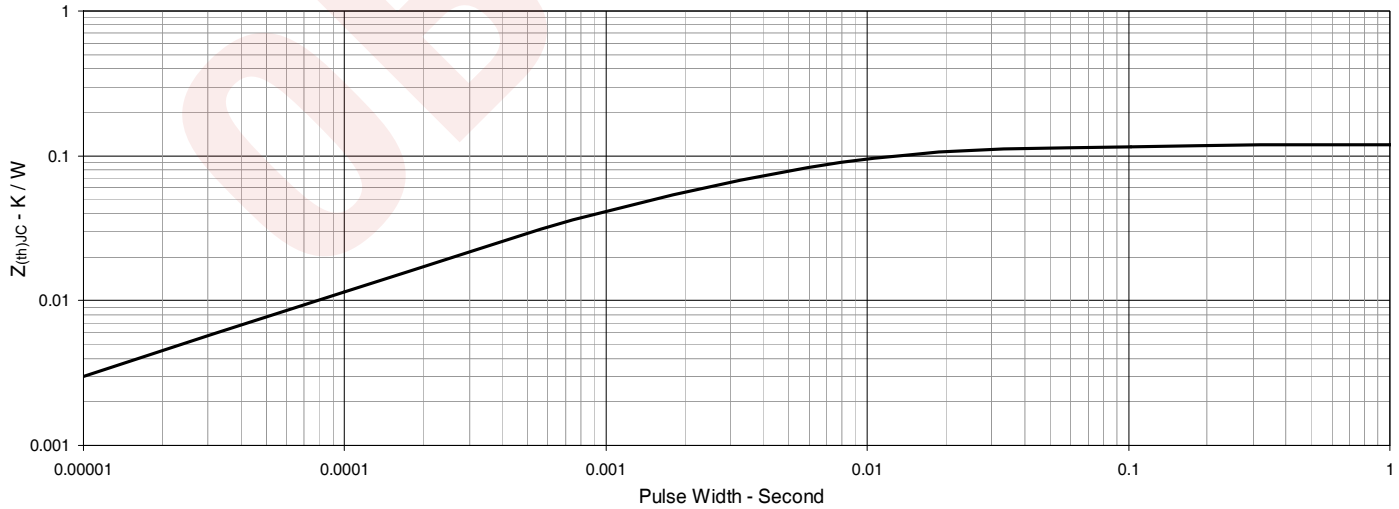


Fig. 11. Maximum Transient Thermal Impedance



IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

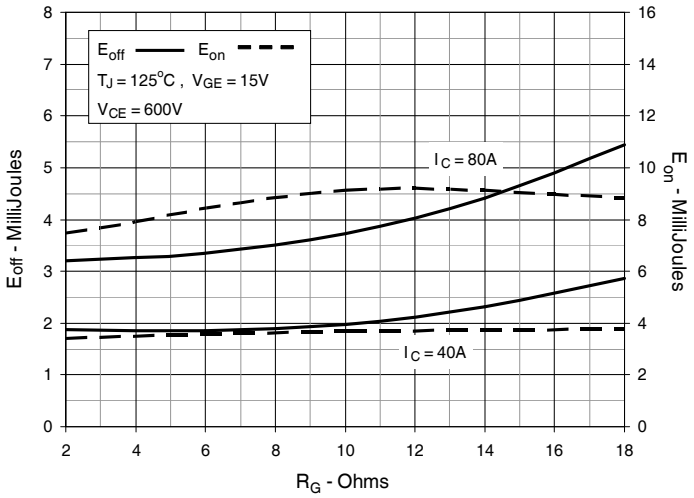


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

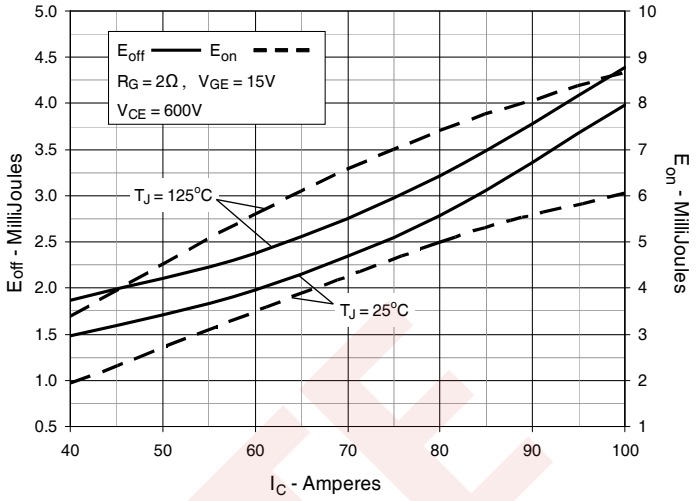


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

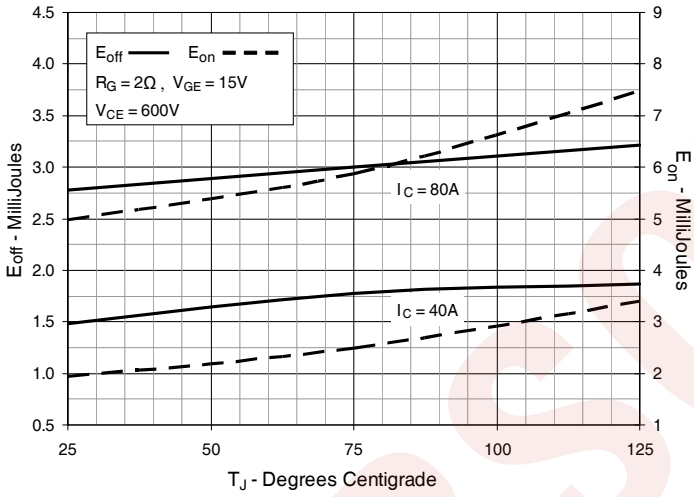


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

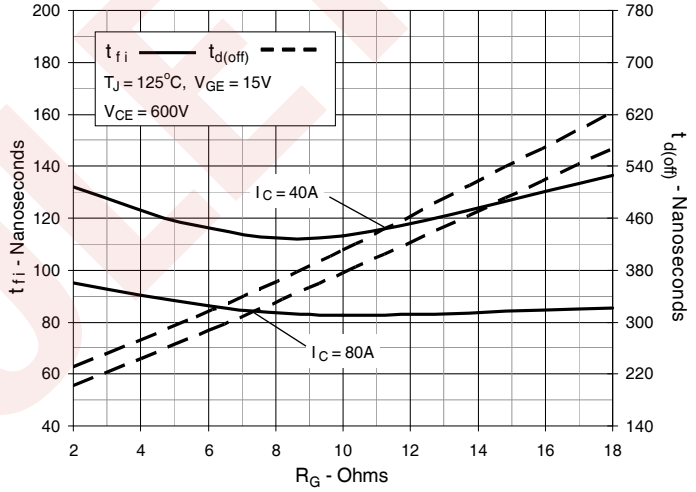


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

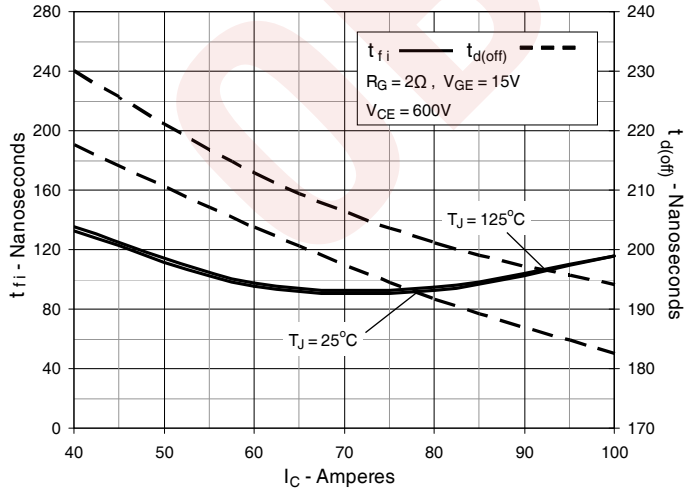


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

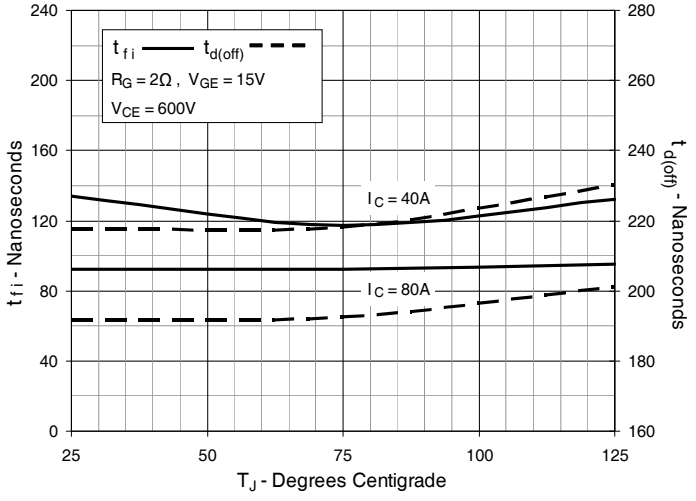


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Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

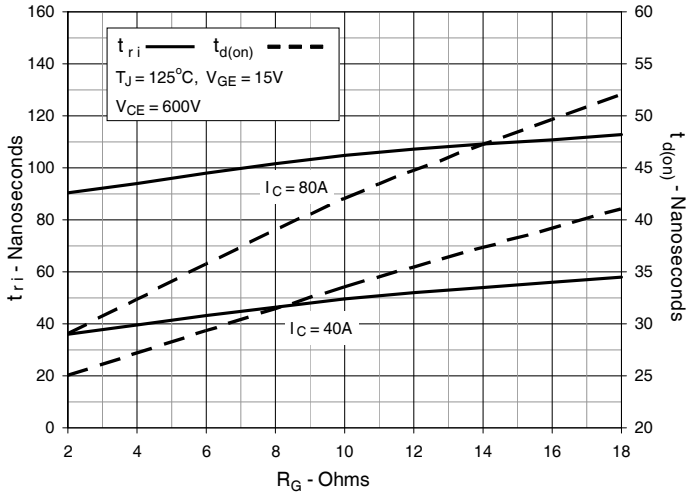

Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

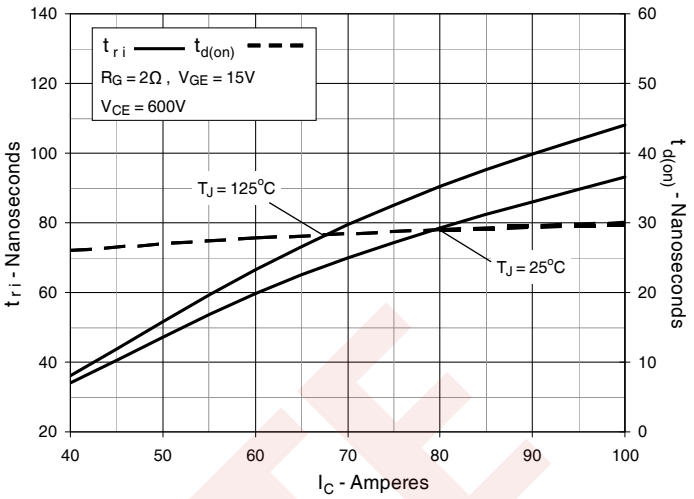

Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

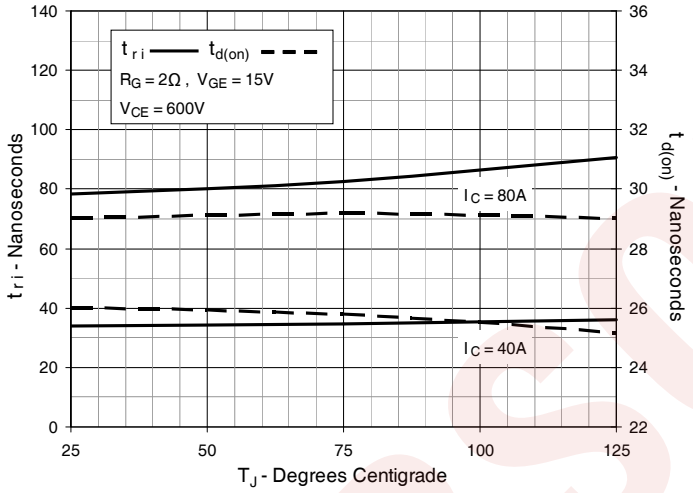

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Fig. 21. Forward Characteristics

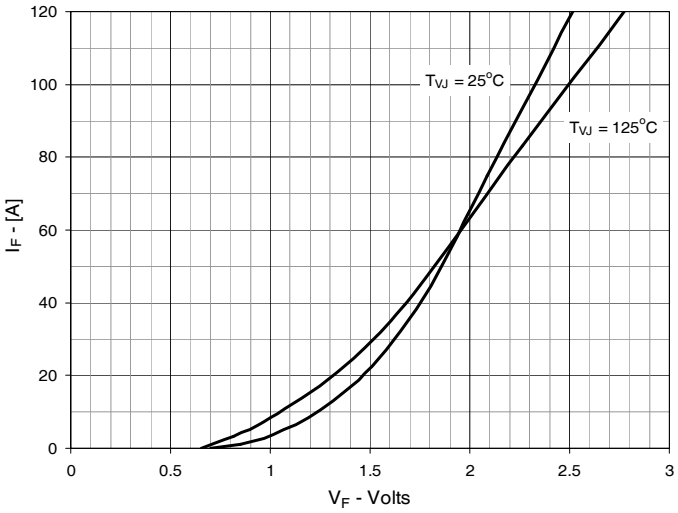


Fig. 22. Reverse Recovery Charge Q_{rr} vs. -di_F/dt

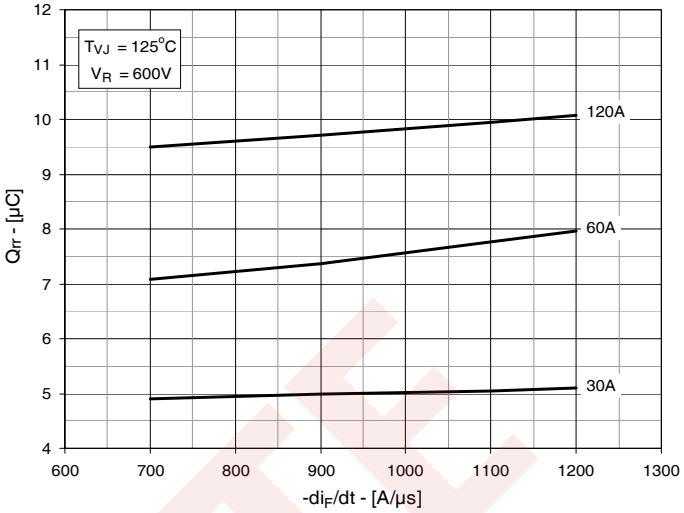


Fig. 23. PeakReverse Current I_{RM} vs. -di_F/dt

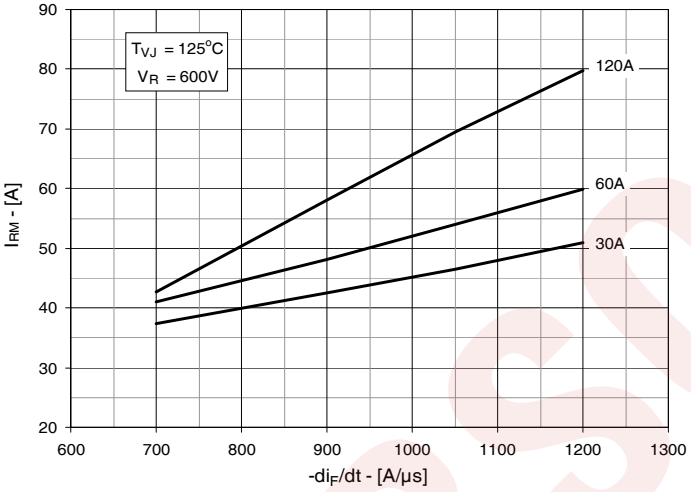


Fig. 24. Recovery Time t_{rr} vs. -di_F/dt

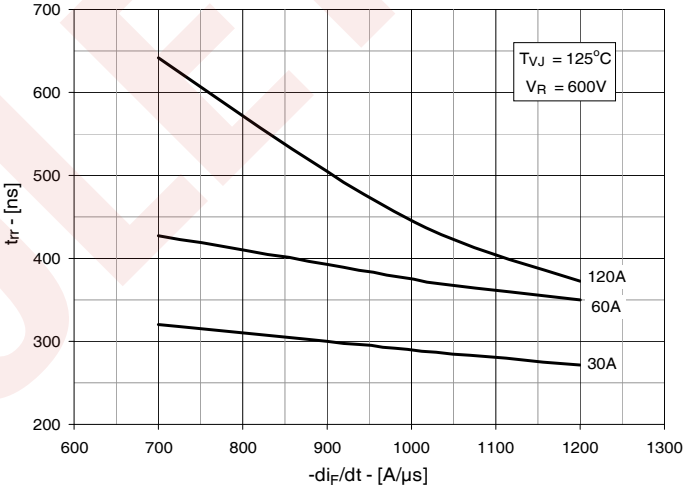


Fig. 25. Recovery Energy E_{rec} vs. -di_F/dt

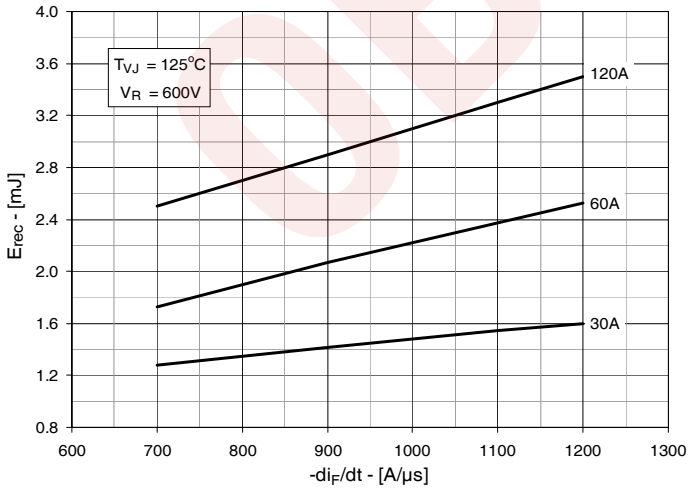
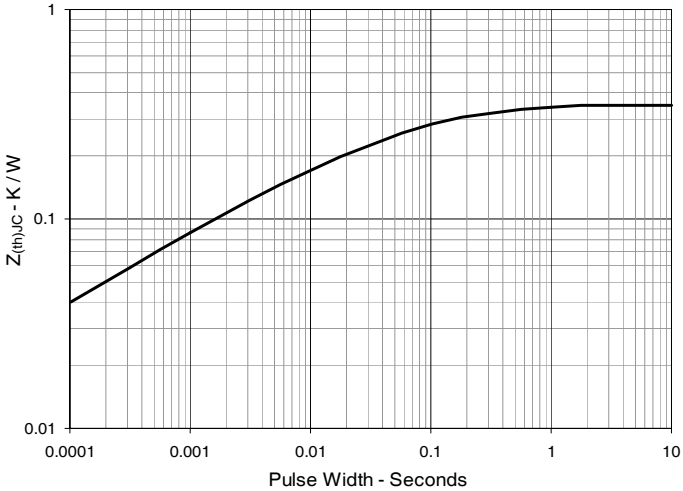


Fig. 26. Maximum Transient Thermal Impedance



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